DATA SHEET

NEC

NPN SILICON RF TRANSISTOR
NE687M33

NPN SILICON RF TRANSISTOR FOR HIGH-FREQUENCY LOW NOISE 3-PIN SUPER LEAD-LESS MINIMOLD (M33)

FEATURES

- Low noise
  NF = 1.5 dB TYP. @ V_{CE} = 1 V, I_C = 3 mA, f = 2 GHz
★ - 3-pin super lead-less minimold (M33) package

ORDERING INFORMATION

Part Number	Quantity	Supplying Form
NE687M33	50 pcs (Non reel)	• 8 mm wide embossed taping
NE687M33-T3	10 kpcs/reel	• Pin 2 (Base) face the perforation side of the tape

Remark To order evaluation samples, contact your nearby sales office.
The unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	5.0	V
Collector to Emitter Voltage	V_{CEO}	3.0	V
Emitter to Base Voltage	V_{EBO}	2.0	V
Collector Current	I_C	30	mA
Total Power Dissipation	P_{tot} Note	90	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	–65 to +150	°C

Note Mounted on 1.08 $cm^2 \times$ 1.0 mm (t) glass epoxy PCB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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The mark ★ shows major revised points.

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I_{CBO}	V_{CB} = 5 V, I_E = 0 mA	–	–	100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 1 V, I_C = 0 mA	–	–	100	nA
DC Current Gain	h_{FE} Note 1	V_{CE} = 1 V, I_C = 10 mA	70	110	140	–
RF Characteristics						
Gain Bandwidth Product	f_T	V_{CE} = 1 V, I_C = 10 mA, f = 2 GHz	10	12	–	GHz
Insertion Power Gain	$\|S_{21e}\|^2$	V_{CE} = 1 V, I_C = 10 mA, f = 2 GHz	7	9	–	dB
Noise Figure	NF	V_{CE} = 1 V, I_C = 3 mA, f = 2 GHz, $Z_S = Z_{opt}$	–	1.5	2.0	dB
Reverse Transfer Capacitance	C_{re} Note 2	V_{CB} = 0.5 V, I_C = 0 mA, f = 1 MHz	–	0.4	0.7	pF

Notes 1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%

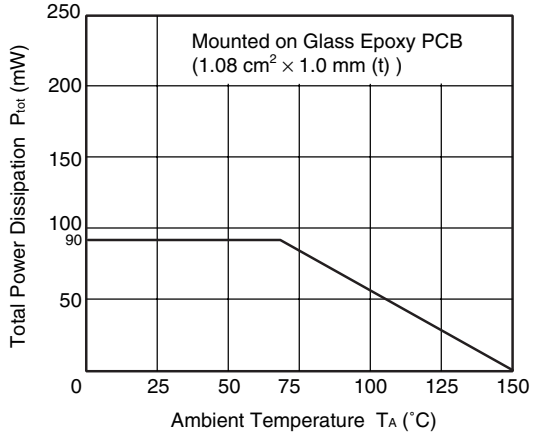
2. Collector to base capacitance when the emitter grounded

h_{FE} CLASSIFICATION

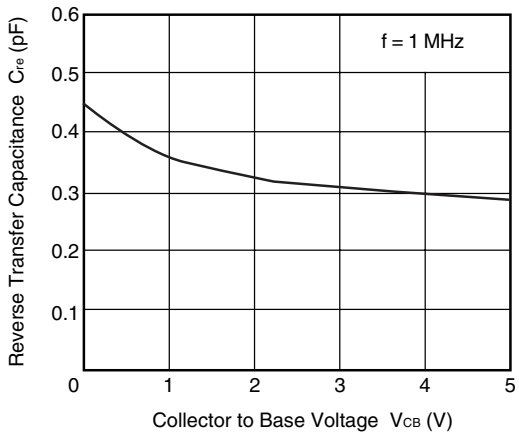
Rank	FB
Marking	W2
h_{FE} Value	70 to 140

★ **TYPICAL CHARACTERISTICS (T_A = +25°C ,unless otherwise specified)**

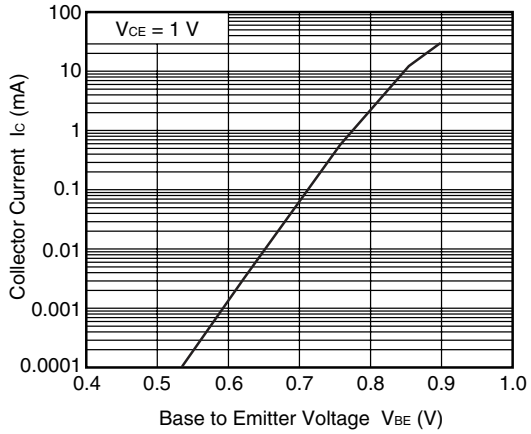
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



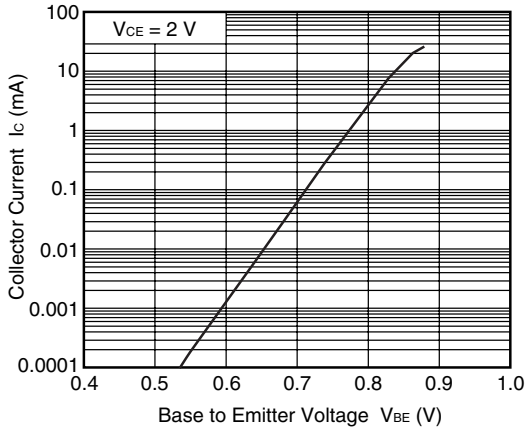
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



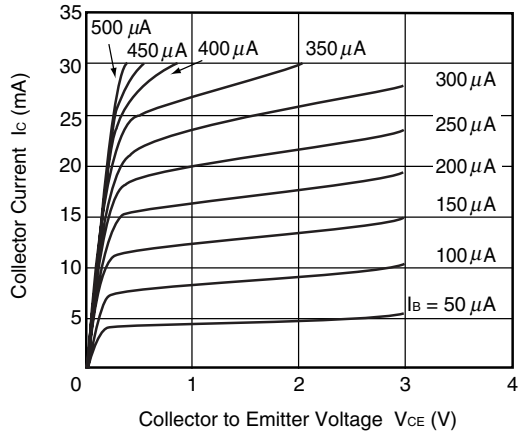
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

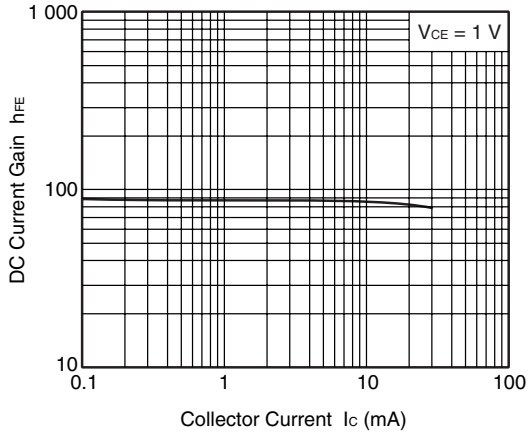


COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

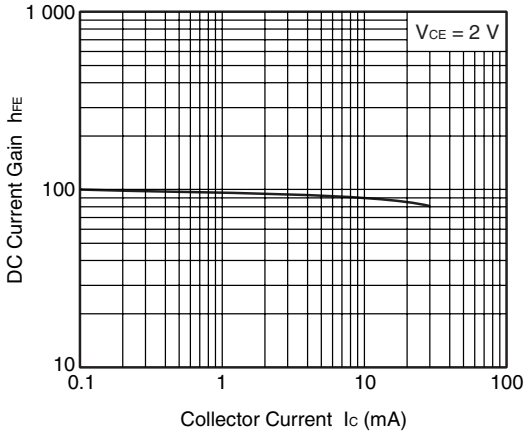


Remark The graphs indicate nominal characteristics.

DC CURRENT GAIN vs.
COLLECTOR CURRENT



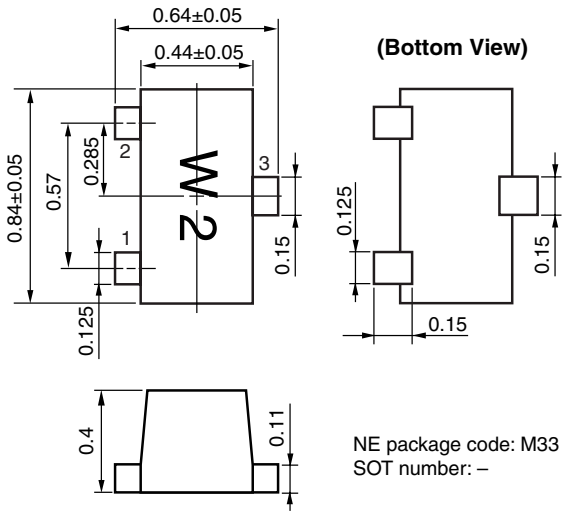
DC CURRENT GAIN vs.
COLLECTOR CURRENT



Remark The graphs indicate nominal characteristics.

PACKAGE DIMENSIONS

3-PIN SUPER LEAD-LESS MINIMOLD (M33) (UNIT: mm)



NE package code: M33
SOT number: –

PIN CONNECTIONS

1. Emitter
2. Base
3. Collector

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